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FIG. 1

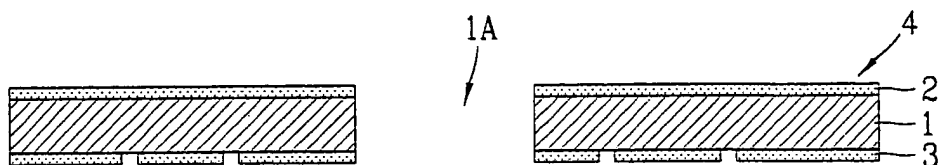


FIG. 2

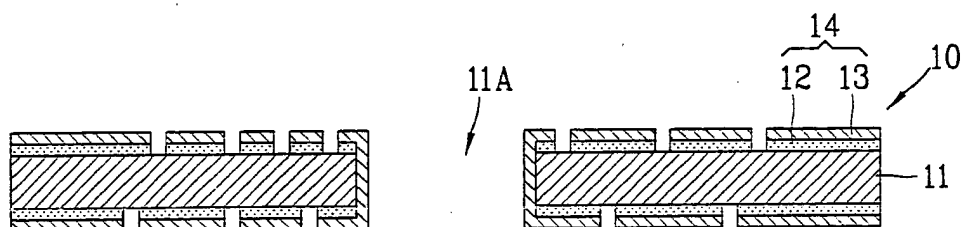


FIG. 3

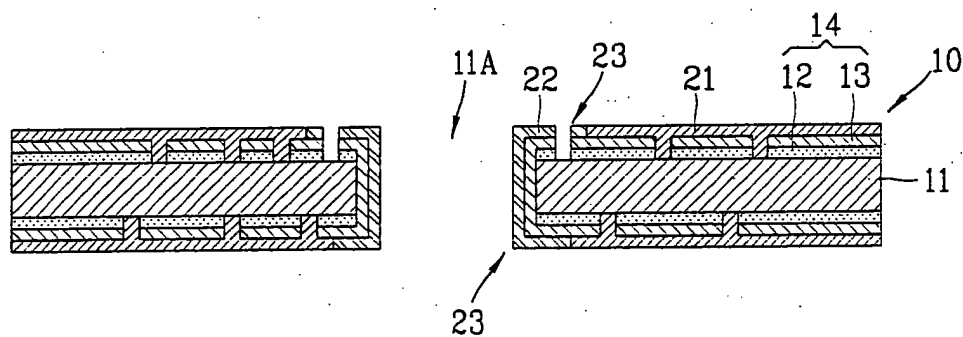
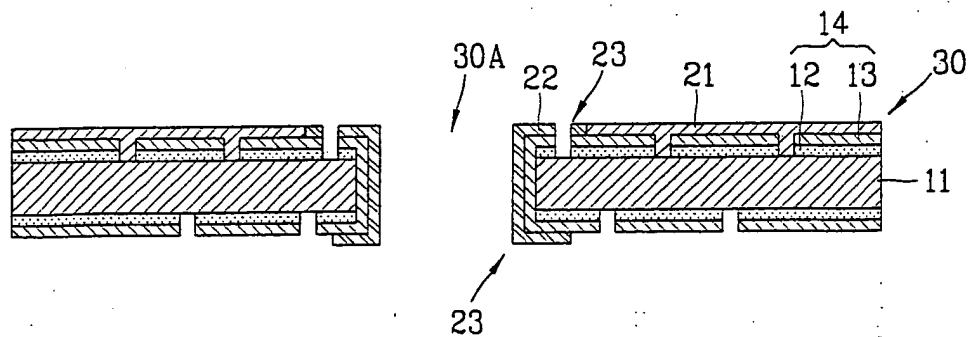


FIG. 4



[illegible]

FIG. 7

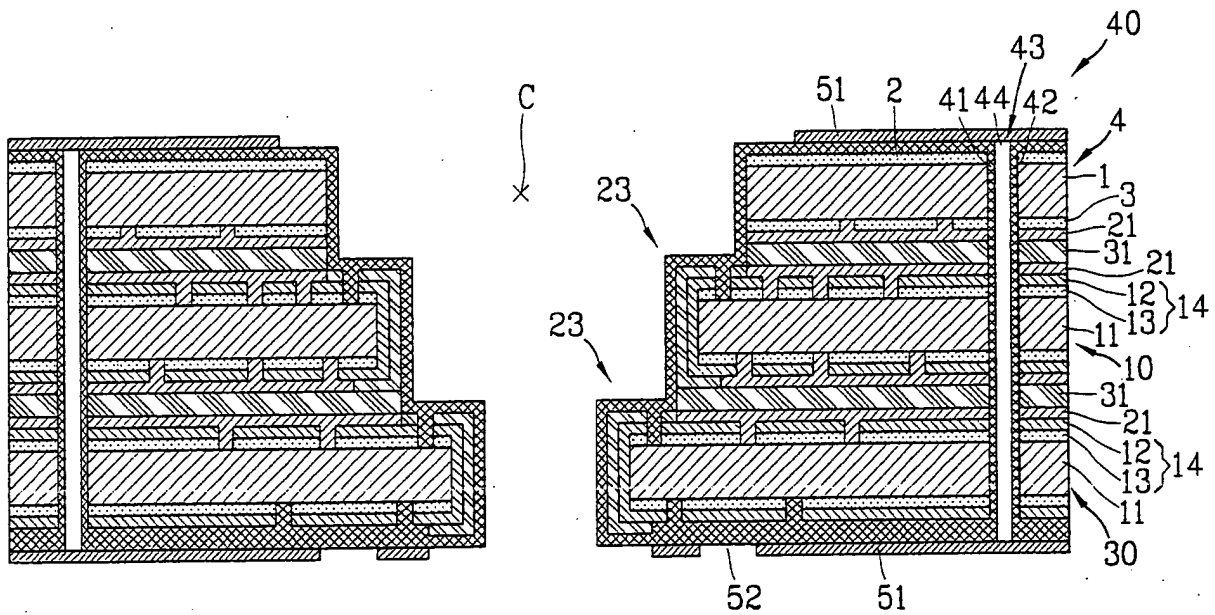
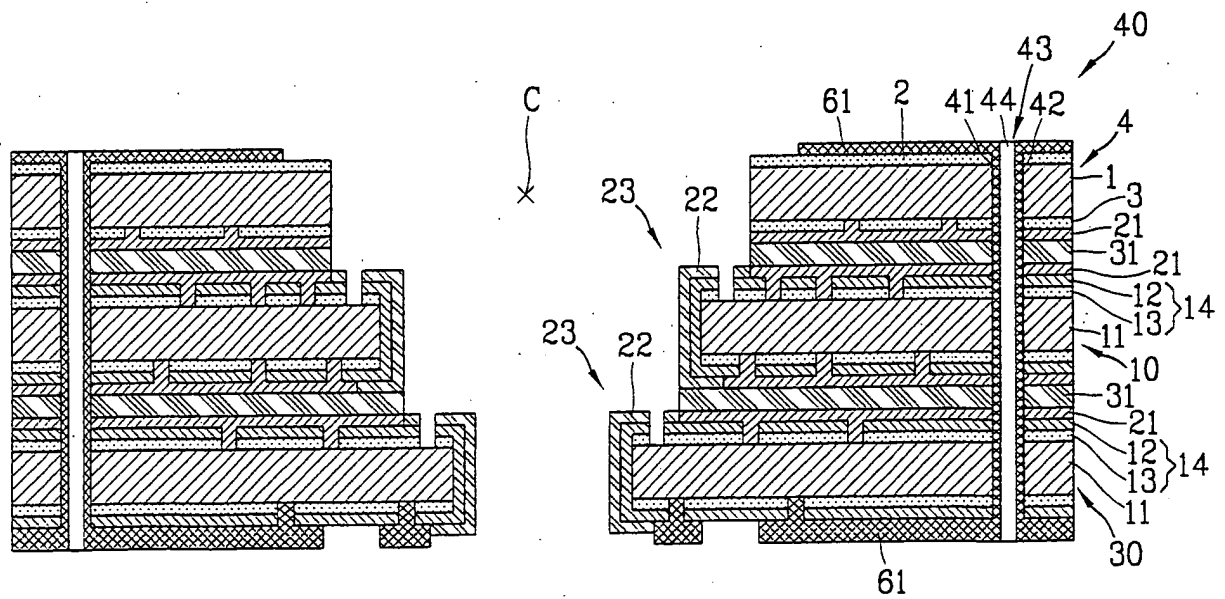


FIG. 8



This cross-sectional diagram shows a multi-layered semiconductor device. A central vertical channel or trench is filled with a material labeled 'C'. The device consists of several horizontal layers with different hatching patterns. On the right side, various components are labeled with numbers: 40 points to the top surface; 4, 1, 3, 21, 31, 12, 13, 11, 10, 31, 21, 12, 13, 11, and 30 label the stacked layers from top to bottom; 14 indicates a group of layers (12, 13); 23 points to two specific structural features on the left and middle; 63, 61, 62, 2, 41, 44, 43, and 42 label additional top-layer features.

FIG. 13

